

Description

The RD74HC04 is a high-speed CMOS HEX INVERTER manufactured using silicon gate CMOS technology.

The internal circuit is composed of 3 stages including a buffer output which enables high noise immunity and stable output.

All inputs are equipped with protection circuits to guard against static discharge and transient excess voltage.

Features

- HIGH SPEED:
 $t_{PD} = 8\text{ns}$ (TYP.) at $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu\text{A}$ (MAX.) at $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\%V_{CC}$ (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 4\text{mA}$ (MIN.) at $V_{CC} = 4.5\text{V}$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 $V_{CC}(\text{OPR.}) = 2\text{V}$ to 6V

Table 1. Device summary

PART NUMBER	PACKAGE
RD74HC04BDI	DIP14
RD74HC04BSO	SOP14
RD74HC04BTS	TSSOP14

1 Pin information

Figure 1. Pin connection and IEC logic symbols

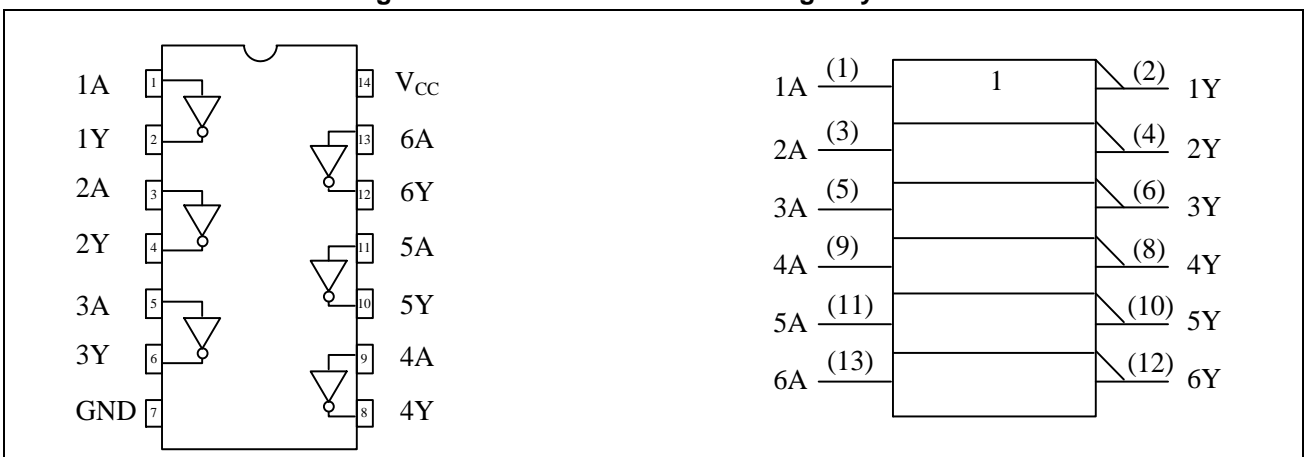


Table 2. Pin description

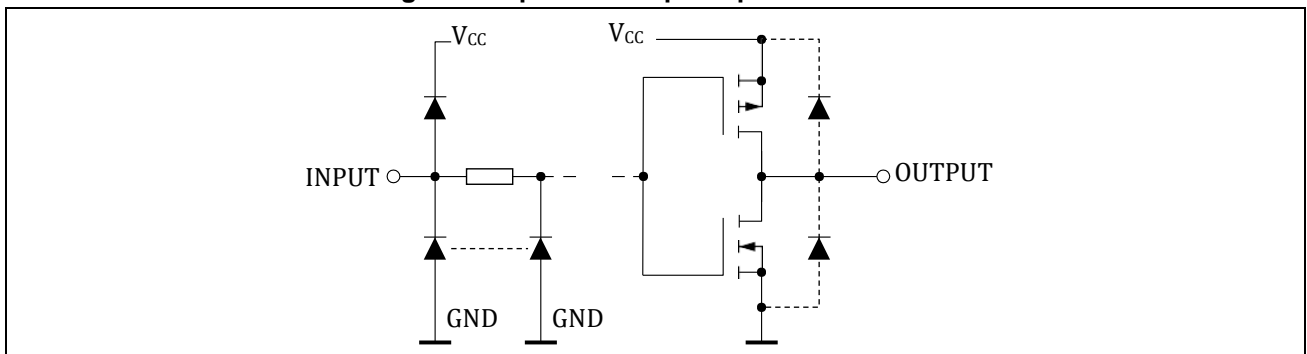
Pin No	Symbol	Name and function
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

2 Functional description

Table 3. Truth table

A	Y
L	H
H	L

Figure 2. Input and output equivalent circuit



3 Electrical characteristics

Stressing the device above the ratings listed in the “Absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only, and operation of the device at these or any other conditions above those indicated in the operating sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to + 7.0	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to + 150	°C
T _L	Lead Temperature (10 sec)	300	°C

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

Table 5. Recommended operating conditions

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature	-40 to +85	°C	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

Table 6. DC specifications

Symbol	Parameter	Test Condition		Value					Unit
		V_{CC} (V)		$T_A = 25^\circ C$			-40 to 85°C		
				Min	Typ	Max	Min	Max	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		V
		4.5		3.15			3.15		
		6.0		4.2			4.2		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5	V
		4.5				1.35		1.35	
		6.0				1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	$I_O = -20\mu A$	1.9	2.0		1.9		V
		4.5	$I_O = -20\mu A$	4.4	4.5		4.4		
		6.0	$I_O = -20\mu A$	5.9	6.0		5.9		
		4.5	$I_O = -4.0 mA$	4.18	4.31		4.13		
		6.0	$I_O = -5.2 mA$	5.68	5.8		5.63		
V_{OL}	Low Level Output Voltage	2.0	$I_O = 20\mu A$		0.0	0.1		0.1	V
		4.5	$I_O = 20\mu A$		0.0	0.1		0.1	
		6.0	$I_O = 20\mu A$		0.0	0.1		0.1	
		4.5	$I_O = 4.0 mA$		0.17	0.26		0.33	
		6.0	$I_O = 5.2 mA$		0.18	0.26		0.33	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1	μA
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			1		10	μA

Table 7. AC electrical characteristics ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

Symbol	Parameter	Test Condition		Value					Unit
		V_{CC} (V)		$T_A = 25^\circ C$			-40 to 85°C		
				Min.	Typ	Max	Min	Max	
t_{TLH}, t_{THL}	Output Transition Time	2.0			38	75		95	ns
		4.5			8	15		19	
		6.0			6	13		16	
t_{PLH}, t_{PHL}	Propagation Delay Time	2.0			45	95		120	ns
		4.5			9	19		24	
		6.0			8	16		20	

Table 8. Capacitive characteristics

Symbol	Parameter	Test Condition		Value					Unit
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		
				Min	Typ	Max	Min	Max	
C _{IN}	Input Capacitance	5.0			5	10		10	pF
C _{PD}	Power Dissipation Capacitance ⁽¹⁾	5.0			22				pF

1. C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to test circuit). Average operating current can be obtained by the following equation:

$$I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6 \text{ (per gate)}$$

4 Test circuit

Figure 3. Test circuit

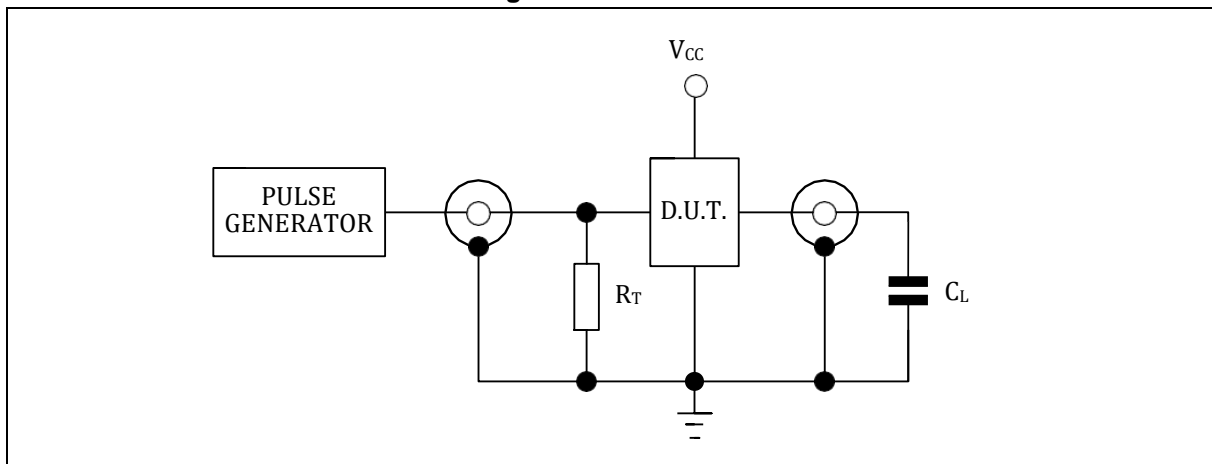
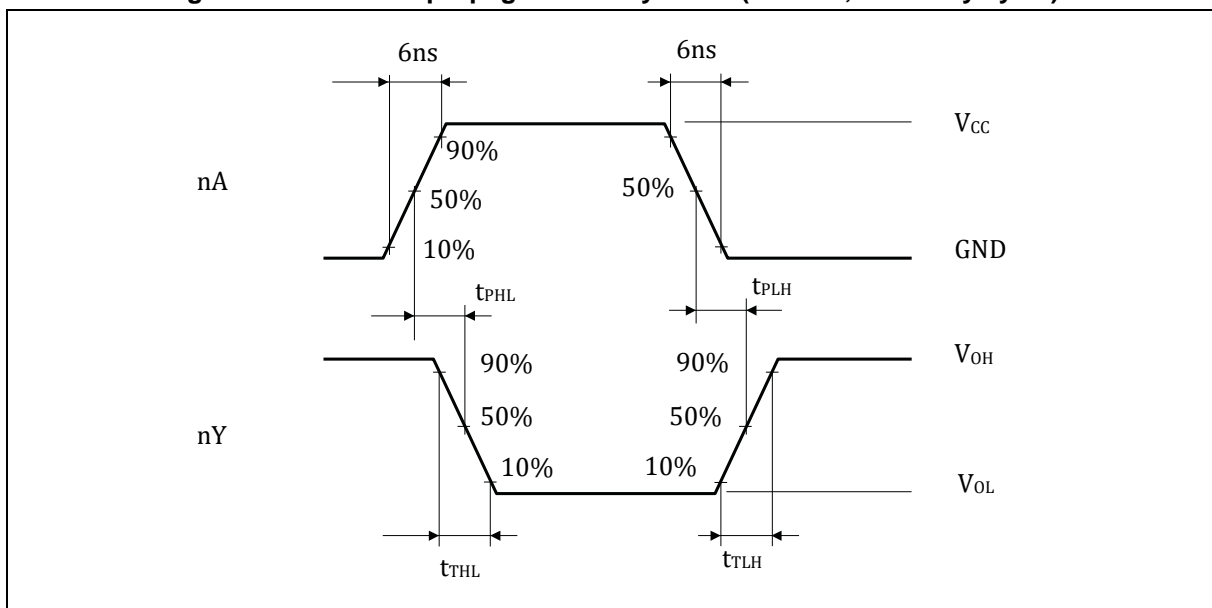


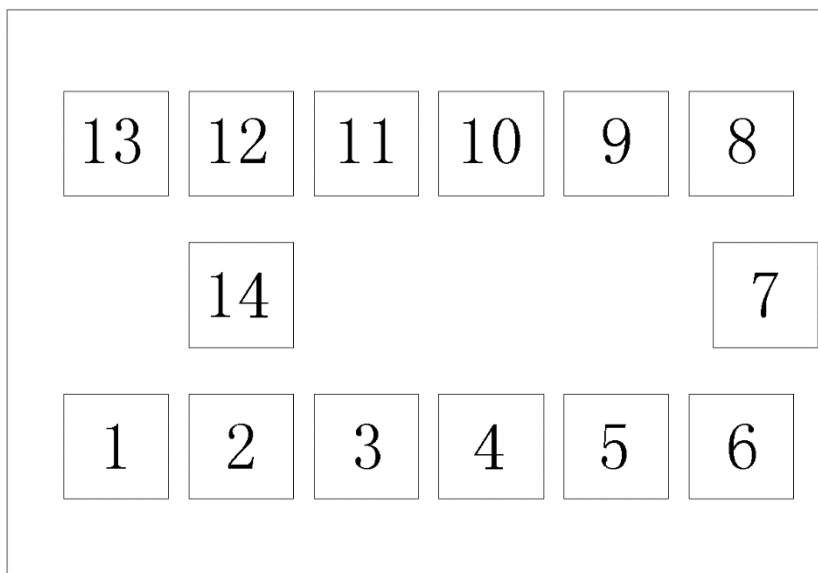
Figure 4. Waveform: propagation delay times (f=1MHz; 50% duty cycle)



5 Die Information

Die Type	RD74HC04	Wafer Size	8 Inch
Die Size (μm)	X/Y:432.6/300	Bond Area (μm)	X/Y: 55/55
Scribeline (μm)	60	Chip Thickness	
Metal	Front	Al+0.5%Cu	
	Back	Si	
	Top Metal Thickness	12000Å	

(432.6, 300.0)



(0, 0)

Pin No.	Pin Name	Coordinate		Pin No.	Pin Name	Coordinate	
		X	Y			X	Y
1	1A	57.3	70.5	8	4Y	386.3	229.5
2	1Y	123.1	70.5	9	4A	320.5	229.5
3	2A	188.9	70.5	10	5Y	254.7	229.5
4	2Y	254.7	70.5	11	5A	188.9	229.5
5	3A	320.5	70.5	12	6Y	123.1	229.5
6	3Y	386.3	70.5	13	6A	57.3	229.5
7	GND	398.95	150.0	14	V _{CC}	123.1	150.0



6 Ordering information

Table 9. Device summary

Order code	Package	Packing
RD74HC04BDI	DIP14	Tape and reel
RD74HC04BSO	SOP14	
RD74HC04BTS	TSSOP14	
RD74HC04B		Wafer

7 Revision history

Table 10. Document revision history ⁽¹⁾

Date	Revision	Changes
18-Jan-2022	1	Initial release
12-Dec-2023	2	Added : Die information Revised document presentation, minor textual updates

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